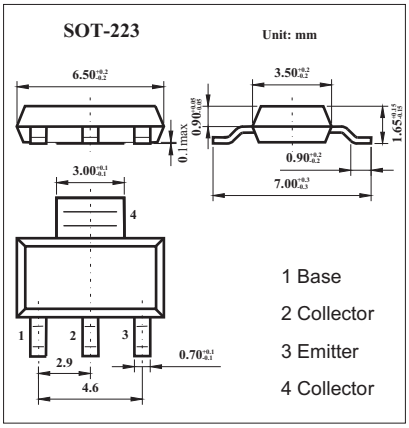
NPN Silicon Planar Medium Power Transistor

FZT491

Features

Power Dissipation: P_C=2W

Continuous Collector Current: I_C=1A



Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	80	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	1	A
power dissipation	P_C	2	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V_{CBO}	I_C=100μA	80			V
Collector to emitter breakdown voltage	V_{CEO}	I_C=10mA	60			V
Emitter to base breakdown voltage	V_{EBO}	I_E=100μA	5			V
Collector cutoff current	I_{CBO}	V_{CB} = 60 V, I_E = 0			100	nA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4V,I_C=0			100	nA
DC current gain	h_{FE}	I_C = 1.0 mA; V_{CE} = 5V	100			
		I_C = 500mA; V_{CE} = 5V	100		300	
		I_C = 1A; V_{CE} = 5V	80			
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = 500mA; I_B = 50mA			0.25	V
		I_C = 1A; I_B = 100mA			0.5	V
Output capacitance	C_{ob}	V_{CB} = 10 V, I_E = 0,f=1.0MHz			10	pF
Transition frequency	f_T	I_C = 50 mA; V_{CE} =10V; f = 100 MHz	150			MHz

Marking

Marking	491